PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of

Takao ABE et al.

Application No.:

09/743,982

Docket No.:

108360

Filed: January 18, 2001

For:

SILICON SINGLE CRYSTAL AND WAFER DOPED WITH GALLIUM AND

METHOD FOR PRODUCING THEM

REQUEST FOR CORRECTION OF PALM RECORDS

Director of the U.S. Patent and Trademark Office Washington, D.C. 20231

Sir:

Attached is a photocopy of the original filing receipt on which errors have been corrected in red. These errors are being brought to the attention of the Patent and Trademark Office so that it may correct its records.

Respectfully submitted,

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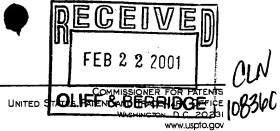
Date: March 21, 2001

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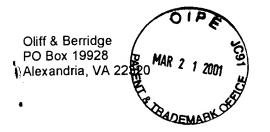
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APPLICATION NUMBER	FILING DATE	GRP ART UNIT	FIL FEE REC'D	ATTY.DOCKET.NO	DRAWINGS	TOT CLAIMS	IND CLAIMS
09/743 982	01/18/2001	1765	914	108360	6	23	3





Date Mailed: 02/20/2001

Receipt is acknowledged of this nonprovisional Patent Application. It will be considered in its order and you will be notified as to the results of the examination. Be sure to provide the U.S. APPLICATION NUMBER, FILING DATE, NAME OF APPLICANT, and TITLE OF INVENTION when inquiring about this application. Fees transmitted by check or draft are subject to collection. Please verify the accuracy of the data presented on this receipt. If an error is noted on this Filing Receipt, please write to the Office of Initial Patent Examination's Customer Service Center. Please provide a copy of this Filing Receipt with the changes noted thereon. If you received a "Notice to File Missing Parts" for this application, please submit any corrections to this Filing Receipt with your reply to the Notice. When the PTO processes the reply to the Notice, the PTO will generate another Filing Receipt incorporating the requested corrections (if appropriate).

Applicant(s)

Takao Abe, Gunma, JAPAN; **Annaka**. Teruhiko Hirasawa, Gunma, JAPAN; **Annaka**. Katsushi Tokunaga, Gunma, JAPAN; **Annaka**. Tetsuya Igarashi, Fukui, JAPAN; **Takefu**. Masafumi Yamaguchi, Aichi, JAPAN; **Naqoya**.

C ntinuing Data as Claimed by Applicant

THIS APPLICATION IS A 371 OF PCT/JP00/02850 04/28/2000

Foreign Applications

JAPAN 11-150697 05/28/1999 JAPAN 11-264549 09/17/1999

If Required, Foreign Filing License Granted 02/20/2001

Title Silicon single Crystal and wafer doped with gallium and method for Gz single crystal doped with ga and wafer and method for producing thereof producing them.

Preliminary Class

117

Data entry by: ORDENEZ, MARTA Team: OIPE Date: 02/20/2001

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